

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (L²-π-MOSV)

2SK2385

HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS

CHOPPER REGULATOR, DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

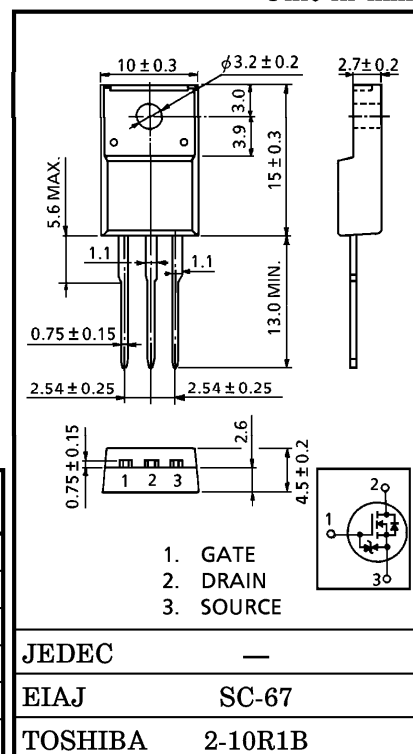
INDUSTRIAL APPLICATIONS

Unit in mm

- 4 V Gate Drive
- Low Drain-Source ON Resistance : $R_{DS(ON)} = 22 \text{ m}\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 27 \text{ S}$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100 \mu\text{A}$ (Max.) ($V_{DS} = 60 \text{ V}$)
- Enhancement-Mode : $V_{th} = 0.8 \sim 2.0 \text{ V}$
($V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$)

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	60	V
Drain-Gate Voltage ($R_{GS} = 20 \text{ k}\Omega$)	V_{DGR}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	DC	I_D	36
	Pulse	I_{DP}	144
Drain Power Dissipation ($T_c = 25^\circ\text{C}$)	P_D	40	W
Single Pulse Avalanche Energy**	E_{AS}	365	mJ
Avalanche Current	I_{AR}	36	A
Repetitive Avalanche Energy*	E_{AR}	4	mJ
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ\text{C}$



Weight : 1.9 g

THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel To Case	$R_{th(ch-c)}$	3.125	$^\circ\text{C/W}$
Thermal Resistance, Channel To Ambient	$R_{th(ch-a)}$	62.5	$^\circ\text{C/W}$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 25 \text{ V}, T_{ch} = 25^\circ\text{C}$ (initial), $L = 383 \mu\text{H}, R_G = 25 \Omega, I_{AR} = 36 \text{ A}$

This transistor is an electrostatic sensitive device.

Please handle with caution.

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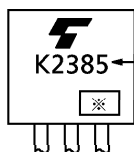
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±16 V, VDS = 0 V	—	—	±10	μA
Drain Cut-off Current		IDSS	VDS = 60 V, VGS = 0 V	—	—	100	μA
Drain-Source Breakdown Voltage		V(BR)DSS	ID = 10 mA, VGS = 0 V	60	—	—	V
Gate Threshold Voltage		Vth	VDS = 10 V, ID = 1 mA	0.8	—	2.0	V
Drain-Source ON Resistance		RDS(ON)	VGS = 4 V, ID = 15 A	—	40	55	mΩ
			VDS = 10 V, ID = 18 A	—	22	30	
Forward Transfer Admittance		Yfs	VDS = 10 V, ID = 18 A	15	27	—	S
Input Capacitance		Ciss	VDS = 10 V, VGS = 0 V, f = 1 MHz	—	1800	—	pF
Reverse Transfer Capacitance		Crss		—	350	—	
Output Capacitance		Coss		—	900	—	
Switching Time	Rise Time	tr		—	20	—	ns
	Turn-on Time	ton		—	30	—	
	Fall Time	tf		—	40	—	
	Turn-off Time	t _{off}		—	130	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 48 V, VGS = 10 V ID = 36 A	—	60	—	nC
Gate-Source Charge		Qgs		—	40	—	
Gate-Drain (“Miller”) Charge		Qgd		—	20	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	36	A
Pulse Drain Reverse Current	IDRP	—	—	—	144	A
Diode Forward Voltage	VDSF	IDR = 36 A, VGS = 0 V	—	—	-1.8	V
Reverse Recovery Time	t _{rr}	IDR = 36 A, VGS = 0 V	—	60	—	ns
Reverse Recovery Charge	Q _{rr}	dIDR / dt = 50 A / μs	—	51	—	nC

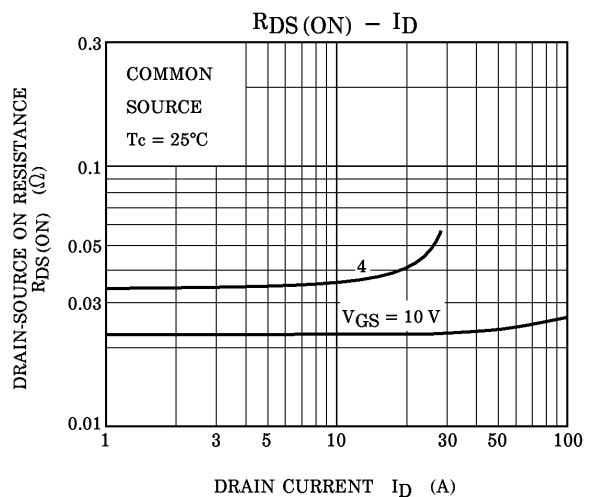
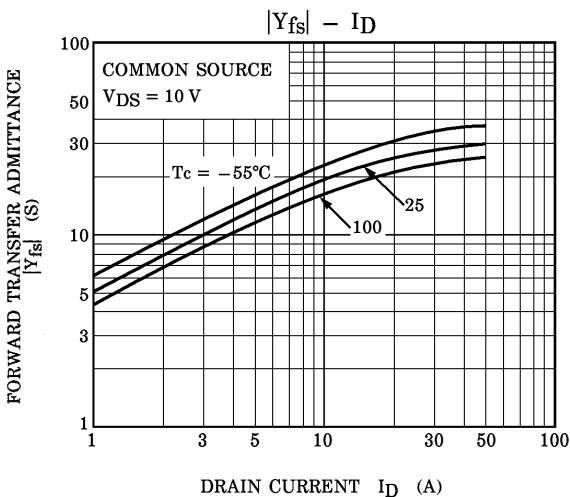
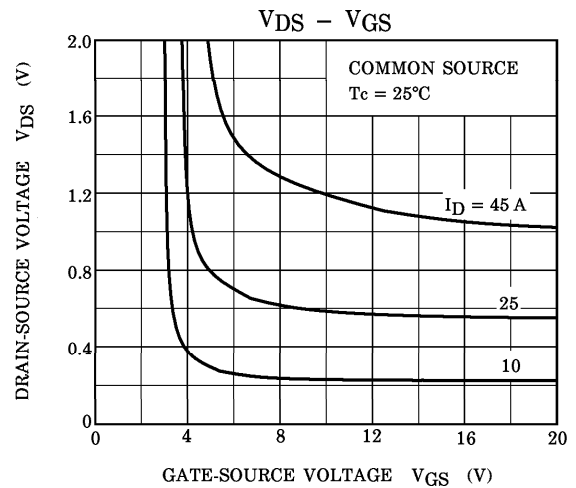
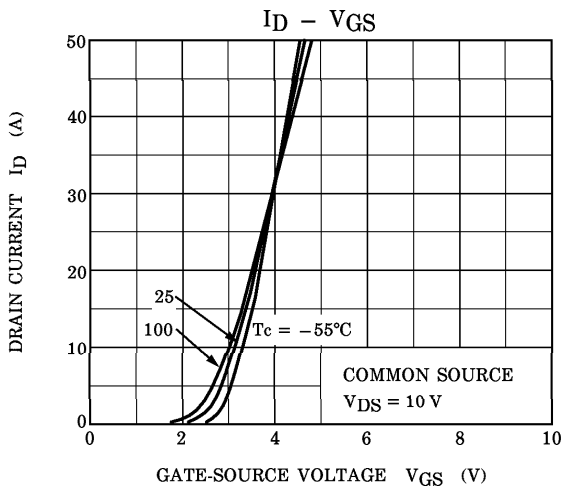
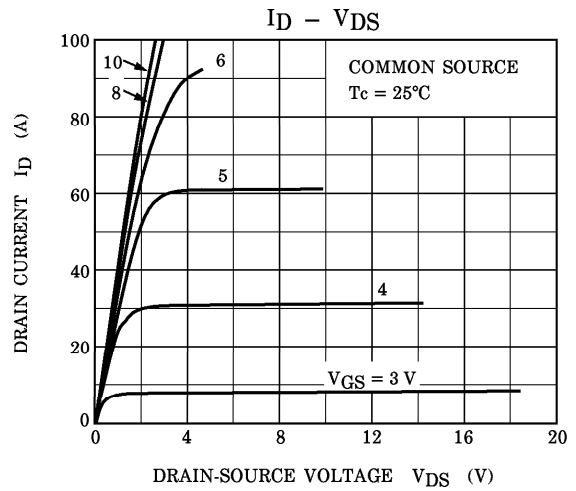
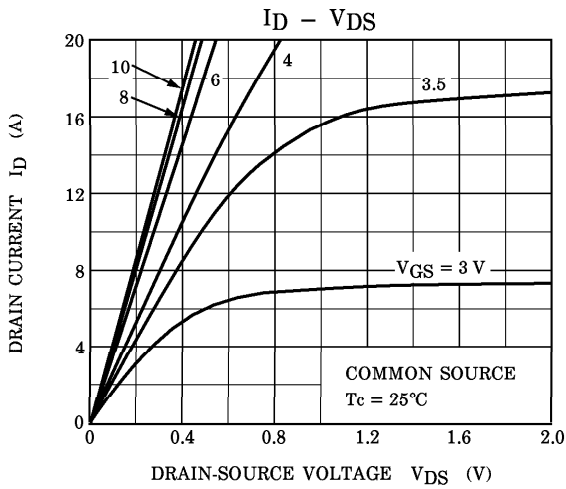
MARKING

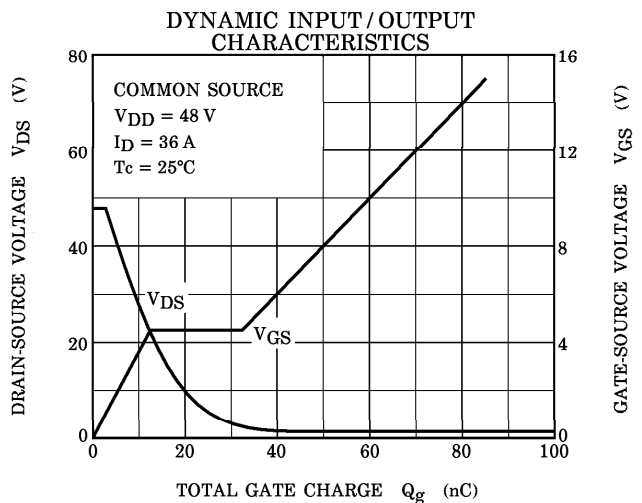
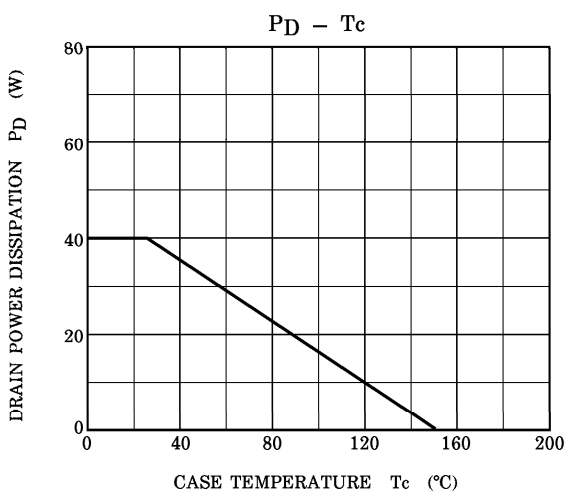
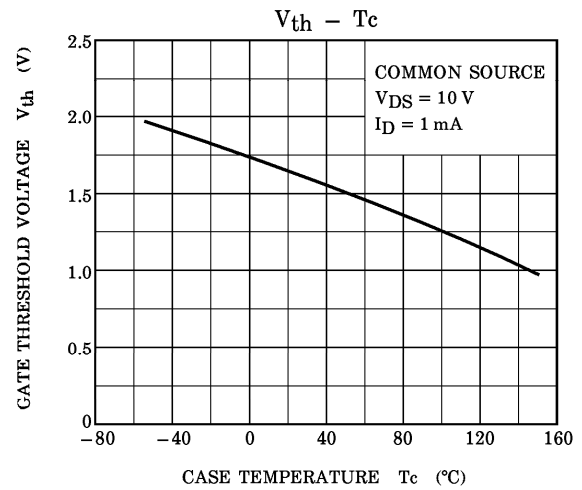
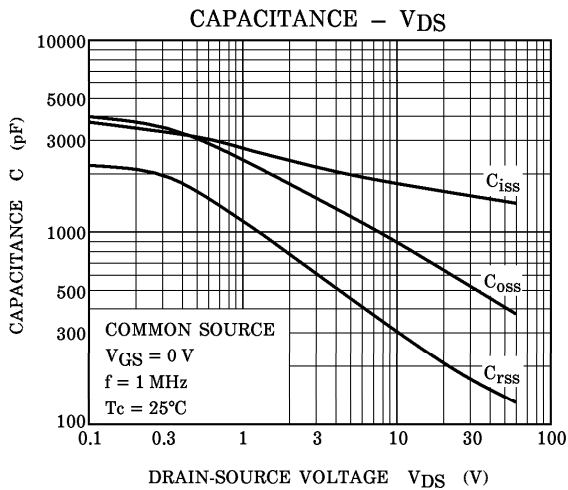
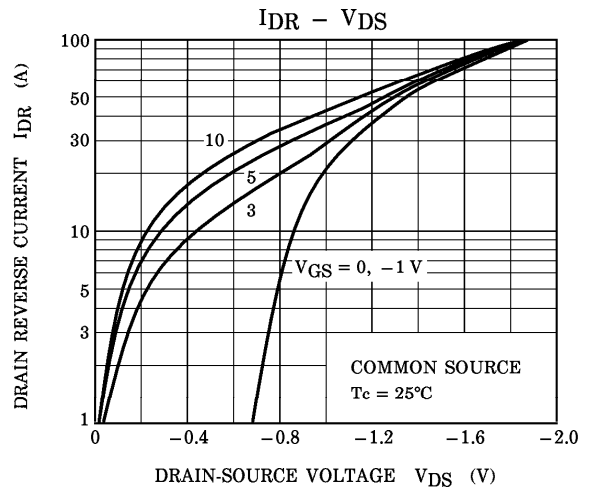
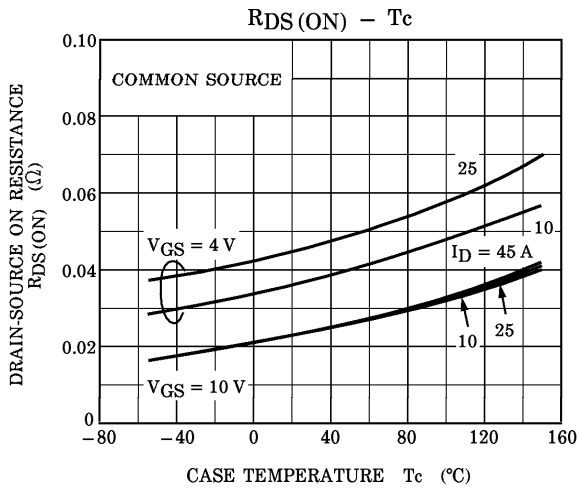


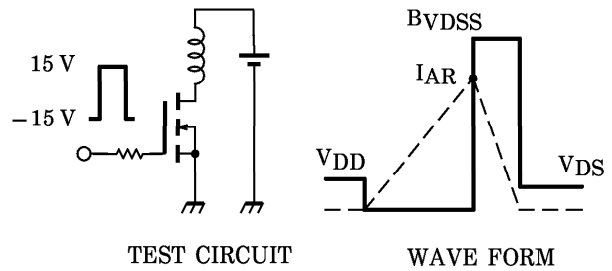
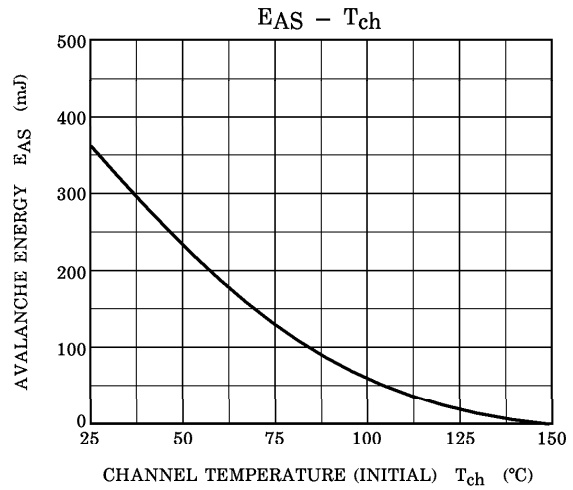
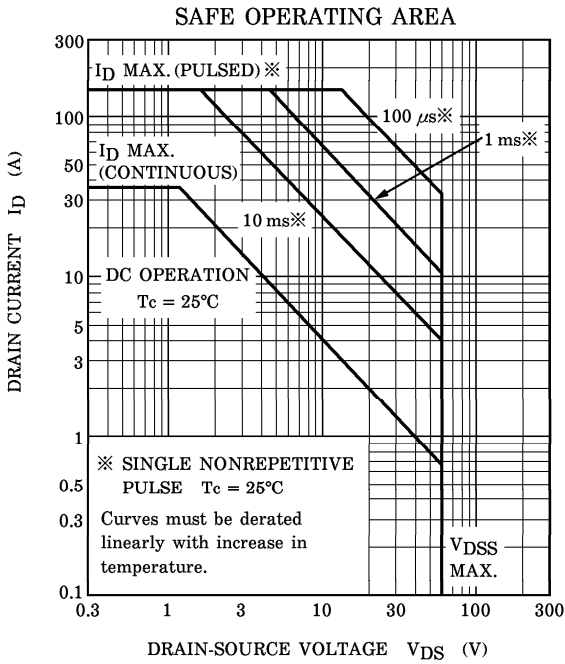
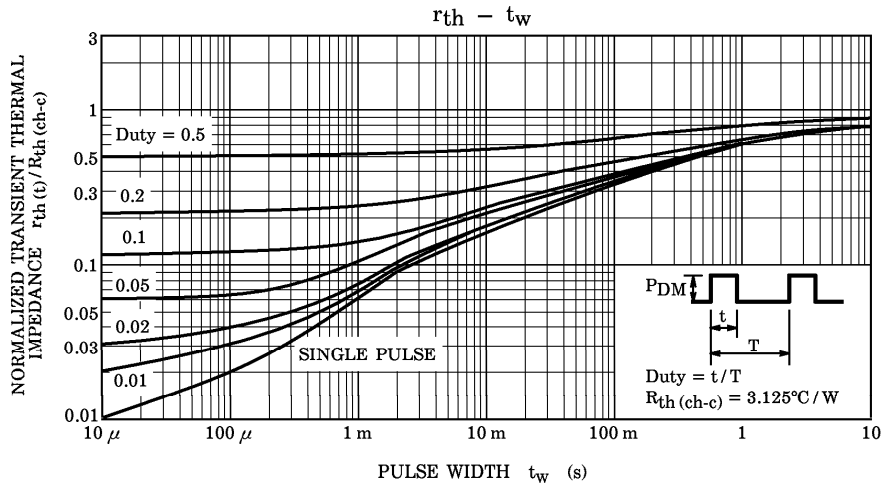
※ Lot Number

□ □ — Month (Starting from Alphabet A)

— Year (Last Number of the Christian Era)







Peak $I_{AR} = 36 \text{ A}$, $R_G = 25 \Omega$, $E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$
 $V_{DD} = 25 \text{ V}$, $L = 383 \mu\text{H}$